L3	17	l2 and (channel near10 polysilicon near10 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:07
L4	5	l2 and (channel near10 polysilicon near10 amorphous).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:08
L5	43	(channel near10 polysilicon near10 amorphous).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:08
L6	0	("2006/0009013").URPN.	USPAT	OR	ON	2006/02/03 17:12
L7	488	(channel with polysilicon with amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:19
L8	61	(channel with polysilicon with amorphous).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:19
L9	21	(channel with (polysilicon near (layer or film or portion or area or region)) with amorphous).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:19
L10	5	(channel with (polysilicon near (layer or film or portion or area or region)) with (amorphous near (layer or film or portion or area or region))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:22
L11	50	(channel with (polysilicon near (layer or film or portion or area or region)) with (amorphous near (layer or film or portion or area or region)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:23
L12	87	(channel and (polysilicon near (layer or film or portion or area or region)) and (amorphous near (layer or film or portion or area or region))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:24

L13	45	(channel and (polysilicon near (layer or film or portion or area or region)) and (amorphous near (layer or film or portion or area or region))).clm. and (tft or (thin near film near transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:24
L14	20	(channel and (polysilicon near (layer or film or portion or area or region)) and (amorphous near (layer or film or portion or area or region))).clm. same (tft or (thin near film near transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:31
L15	0	(amorphous adj portion).clm. and (polysilicon adj portion).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:33
L16	17	(amorphous near\ portion).clm. and (polysilicon adj portion).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:33
L17	5	(amorphous near portion).clm. and (polysilicon adj portion).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:33
L18	17	(amorphous near portion).clm. and (polysilicon near portion).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:33
L19	5	(amorphous near portion).clm. and (polysilicon near portion).clm. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:46
L20	294	(low near temperature near polysilicon near thin near film near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:46
L21	66	(low near temperature near polysilicon near thin near film near transistor) and gate.clm. and channel.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 17:46